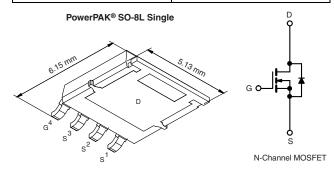


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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0039			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0042			
I _D (A)	32			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_a and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ410EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	s otherwise noted	i)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Currenta	T _C = 25 °C	1	32	
Continuous Diain Current-	T _C = 125 °C	I _D	32	
Continuous Source Current (Diode Conduction	n) ^a	Is	32	Α
Pulsed Drain Current ^b		I _{DM}	128	
Single Pulse Avalanche Current	J 0.1 ml J	I _{AS}	58	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	168	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	D	83	W
viaximum Fower Dissipation	T _C = 125 °C	P _D	27	VV
Operating Junction and Storage Temperature	T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)e, f			260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	65	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.8	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See Solder Profile (www.vishay.com/doc?73257). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							ı
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V _{GS} = 10 V	I _D = 10.3 A	-	0.0037	0.0039	
Drain Cauras On State Resistance		V _{GS} = 10 V	I _D = 10.3 A, T _J = 125 °C	-	0.0045	0.0060	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10.3 A, T _J = 175 °C	-	0.0055	0.0070	Ω
		V _{GS} = 4.5 V	I _D = 8.7 A	-	0.0035	0.0042	1
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 16 A		-	93	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	4965	6210	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 15 V, f = 1 MHz	-	806	1010	pF
Reverse Transfer Capacitance	C _{rss}	1		-	325	410	
Total Gate Charge ^c	Qg			-	73.5	110	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 15 \text{ A}$	-	12.8	-	nC
Gate-Drain Charge ^c	Q _{gd}]		-	8.2	=-	
Gate Resistance	R _g	f = 1 MHz		0.6	1.0	1.4	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	23	
Rise Time ^c	t _r	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	40	60	
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Char-	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	128	Α
Forward Voltage	V _{SD}	I _F :	= 10 A, V _{GS} = 0	-	0.75	1.2	V

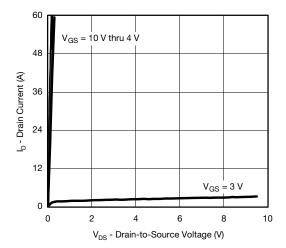
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

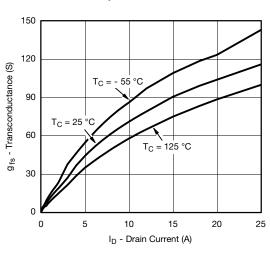
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



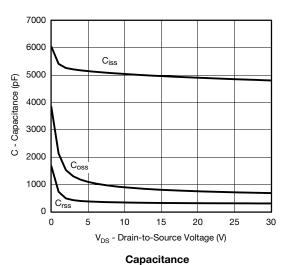
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics

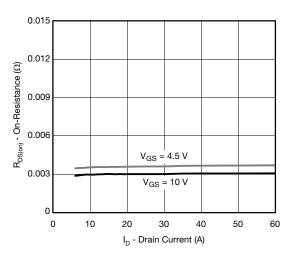


Transconductance

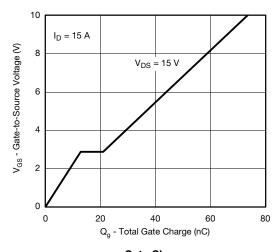


60 48 I_D - Drain Current (A) 36 24 $T_{C} = 25$ 12 125 T_C = - 55 °C T_C = 0 0 5 2 3 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

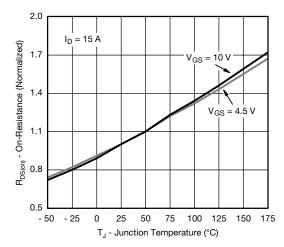


On-Resistance vs. Drain Current

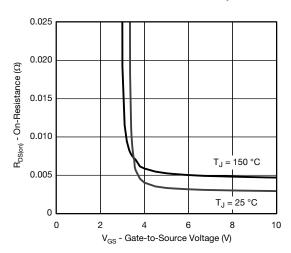




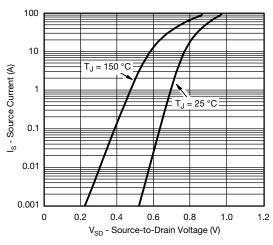
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



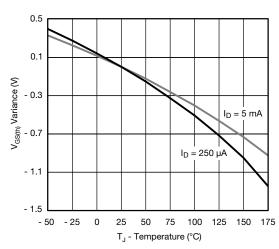
On-Resistance vs. Junction Temperature



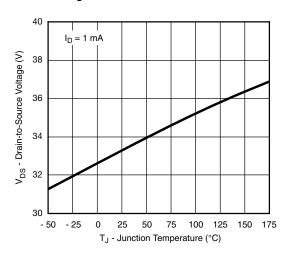
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



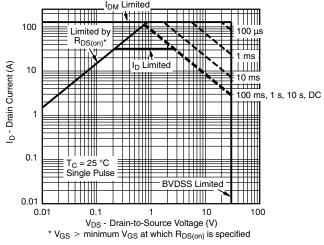
Threshold Voltage



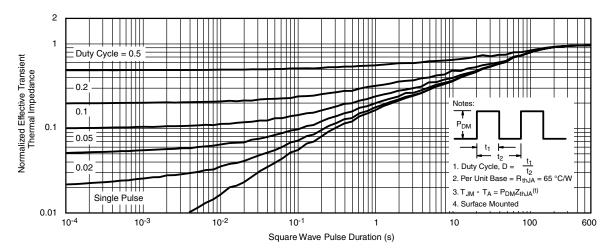
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



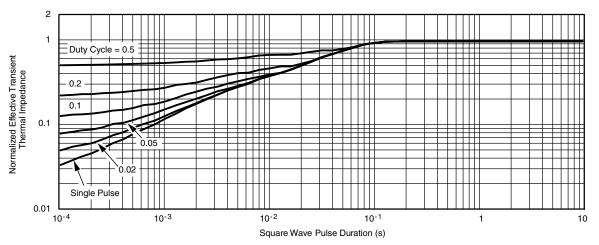
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

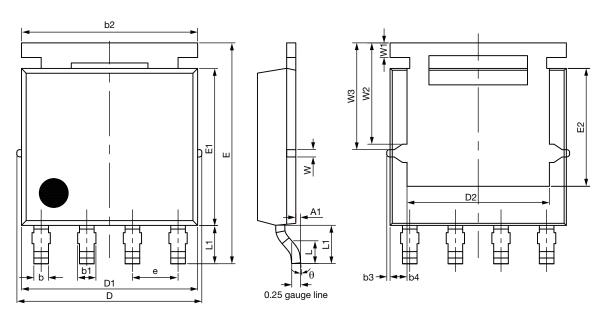
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267003.

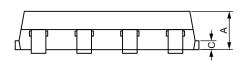
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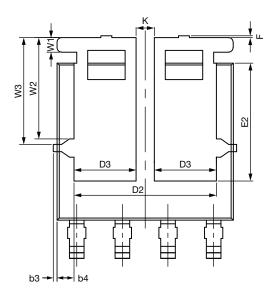
PowerPAK® SO-8L Case Outline for Non-Al Parts



Topside view

Backside view (single)





Backside view (dual)





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D.11.4	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
Α	1.00	1.07	1.14	0.039	0.042	0.04	
A1	0.00	-	0.127	0.00	-	0.00	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.13	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2		2.82			0.111		
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: T16-0221-Rev. D, 16-May-16

DWG: 5976

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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